

YSZ Interconnect Barriers via ALD

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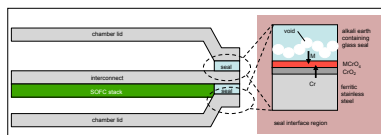
25 Francis J Clarke Circle, Bethel, CT 06801

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FuelCell Energy, Inc.

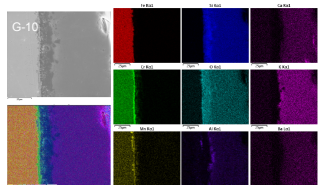
3 Great Pasture Road, Danbury, CT 06810

Need for Interconnect Barrier

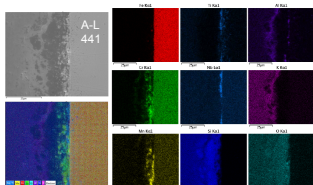


Improved barriers are needed to extend operating lifetime of glass sealed interconnects in SOFC stacks

- Alkali-earth (M=Mg, Ca, Sr, Ba) cations in seal glass react with Cr in stainless steel
- Form $MCrO_x$ chromites; other aluminosilicates and Mn-Cr-O due to segregation effects
- Leave vacancies that coalesce to voids
- Void leads to leaks in seals
- YSZ has shown promise as an effective barrier material*



Reaction of ferritic stainless steels with SEM-CON-SCN-01
850°C
260 hr.



*R.N. Singh, "Innovative Self Healing Seals for Solid Oxide Fuel Cells," 12th Annual SOFC Workshop, Pittsburgh, PA, July 26, 2011

YSZ ALD Process



Precursor chemistry:

- Volatile
- Thermally stable
- Zr source widely used for DRAM manufacturing
- Highly reactive with water as oxidizing agent

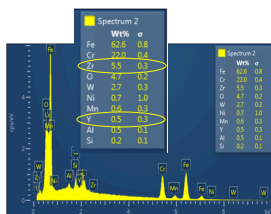


Process conditions:

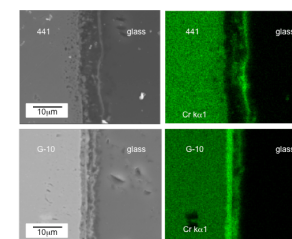
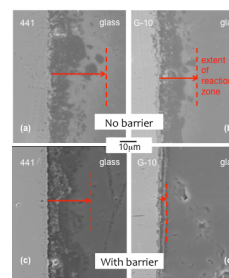
- Deposition temperature 230°C
- Deposition pressure 1 Torr

Process recipe:

- 9:1 ratio of Zr to Y cycles
- Film composition ~ 11.5:1 (Zr:Y)



Barrier Performance

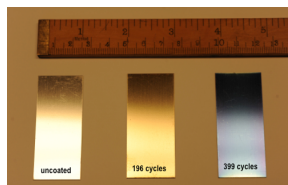
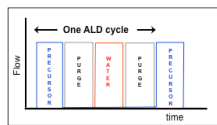
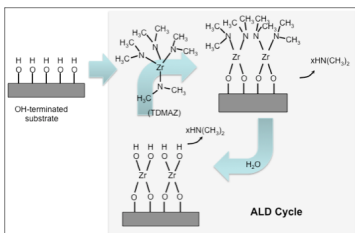


- 441 sample showed evidence of spallation
- Hitachi G-10 had robust Cr_2O_3 layer
- Phase II will examine effects of surface condition in combination with barrier optimization
- Significant reduction in reaction with YSZ barrier
- (800 cycles)
- Surface of stainless steel has an effect

Novel Interconnect Barrier Approach: ALD YSZ

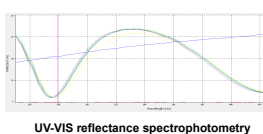
ALD is a simple, highly self-regulating process that uses precursors and reactants separated by an inert gas (N_2)

- Surface saturation limiting of precursor dose
- Reactants fed into reactor in a pulse train

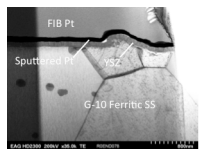


- Highly uniform thickness achieved (<1% sigma)
- Uniformity observed over length scale of full sized interconnects

TEM
800 cycle YSZ film



UV-VIS reflectance spectrophotometry



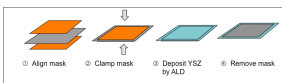
λ (nm)	Distance from end (mm)
277	5
274	15
275	25
275	35
276	45
278	55
279	65

Mean StDev (%) 1.80
StDev (%) 0.65%

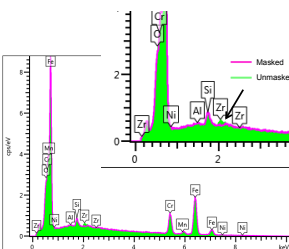
76 mm

Masking

Barrier coating must be limited to perimeter of interconnect



- Novel, reusable mask strategy identified
- Stackable for high volume manufacturing



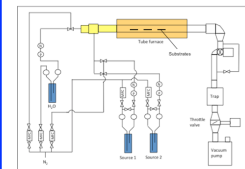
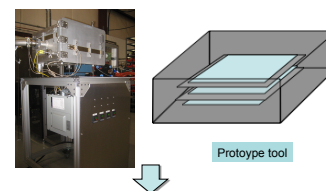
- Silicone mask
- High thermal stability

From Research to Manufacturing

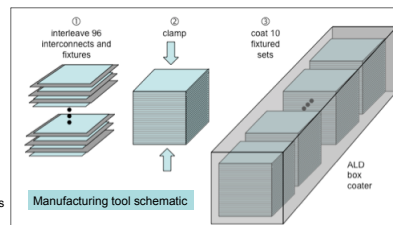


R&D ALD tool uses a 50mm tube furnace

Prototype tool will allow coating of full size interconnects



Manufacturing tool takes advantage of highly scalable batch processing of ALD → Current systems coat very large area (thousands of m²) in high volume manufacturing environments



Acknowledgements

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